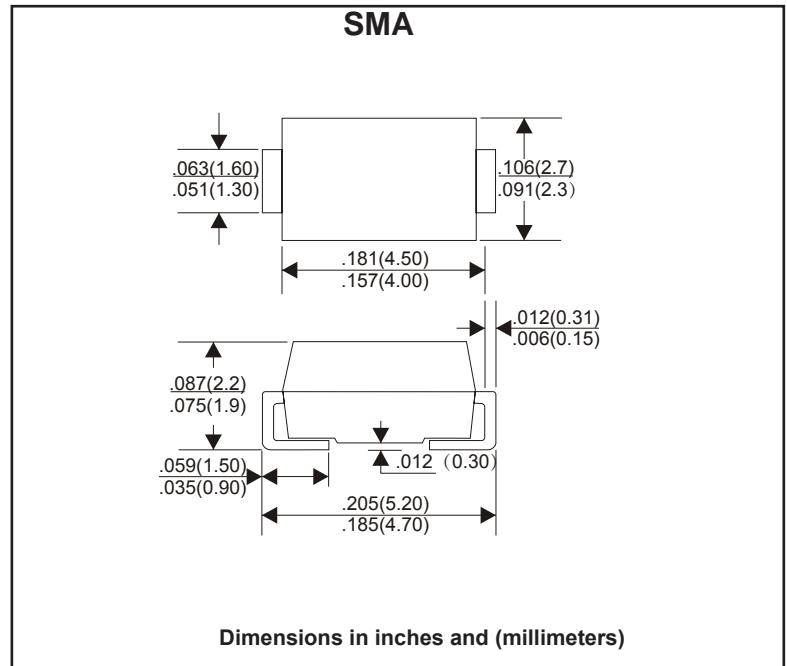


FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Easy to pick and place
- High efficiency
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

- Case: SMA
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.055g / 0.002oz



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted) Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate by 20%.

Parameter	Symbols	US1A	US1B	US1D	US1G	US1J	US1K	US1M	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_c = 125^\circ\text{C}$	$I_{F(AV)}$	1							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I_{FSM}	30							A
Maximum Instantaneous Forward Voltage at 1 A	V_F	1.0		1.3		1.65		V	
Maximum DC Reverse Current at Rated DC Blocking Voltage	I_R	5 100							μA
Maximum Reverse Recovery Time ⁽¹⁾	t_{rr}	50				75			ns
Typical Thermal Resistance ⁽²⁾	R_θ	75							$^\circ\text{C}/\text{W}$
Typical Junction Capacitance ⁽³⁾	C_j	15							pF
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150							$^\circ\text{C}$

(1) Measured with $I_F = 0.5\text{ A}$, $I_R = 1\text{ A}$, $I_{rr} = 0.25\text{ A}$

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

(3) Measured at 1 MHz and applied reverse voltage of 4 V D.C



RATINGS AND CHARACTERISTIC CURVES

Fig.1 Forward Current Derating Curve

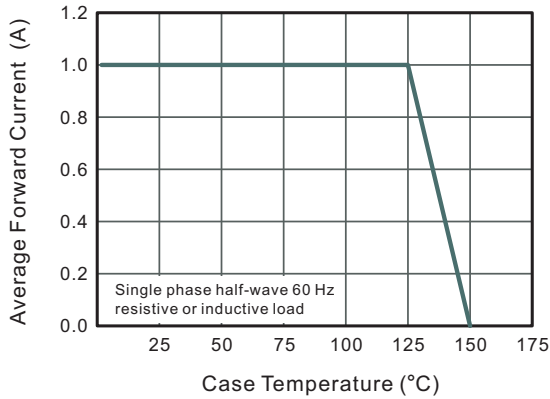


Fig.2 Typical Reverse Characteristics

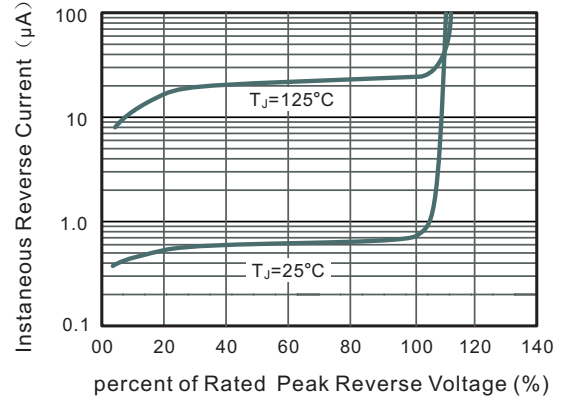


Fig.3 Typical Forward Characteristics

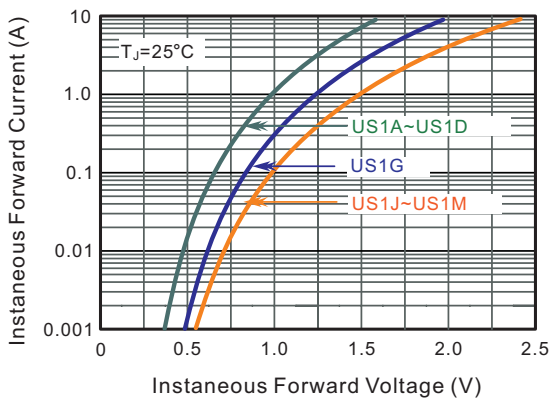


Fig.4 Maximum Non-Repetitive Peak Forward Surge Current

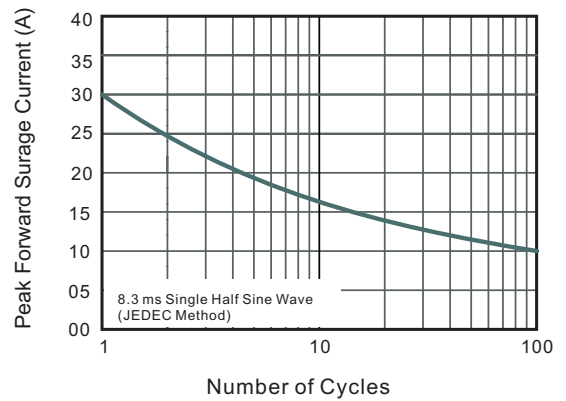


Fig.5- Typical Transient Thermal Impedance

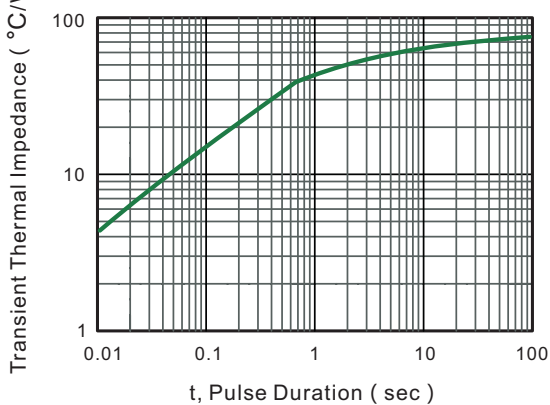


Fig.6 Typical Junction Capacitance

